

# Michael J Manfra

## List of Publications by Year in descending order

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178  
papers

6,757  
citations

66234

42  
h-index

74018

75  
g-index

178  
all docs

178  
docs citations

178  
times ranked

5665  
citing authors

#	ARTICLE	IF	CITATIONS
1	Supercurrent rectification and magnetochiral effects in symmetric Josephson junctions. Nature Nanotechnology, 2022, 17, 39-44.	15.6	134
2	Domain Textures in the Fractional Quantum Hall Effect. Physical Review Letters, 2022, 128, 017401.	2.9	1
3	Impact of bulk-edge coupling on observation of anyonic braiding statistics in quantum Hall interferometers. Nature Communications, 2022, 13, 344.	5.8	11
4	Effect of Rashba and Dresselhaus spin-orbit coupling on supercurrent rectification and magnetochiral anisotropy of ballistic Josephson junctions. Journal of Physics Condensed Matter, 2022, 34, 154005.	0.7	39
5	A Robust Protocol for Entropy Measurement in Mesoscopic Circuits. Entropy, 2022, 24, 417.	1.1	10
6	Novel nitride quantum structures for infrared sensing. , 2022, , .		0
7	Measurements of cyclotron resonance of the interfacial states in strong spin-orbit coupled 2D electron gases proximitized with aluminum. Applied Physics Letters, 2022, 120, 142105.	1.5	4
8	Clean quantum point contacts in an InAs quantum well grown on a lattice-mismatched InP substrate. Physical Review B, 2022, 105, .	1.1	2
9	Microwave sensing of Andreev bound states in a gate-defined superconducting quantum point contact. Physical Review Research, 2022, 4, .	1.3	2
10	A cryogenic CMOS chip for generating control signals for multiple qubits. Nature Electronics, 2021, 4, 64-70.	13.1	105
11	Josephson Inductance as a Probe for Highly Ballistic Semiconductor-Superconductor Weak Links. Physical Review Letters, 2021, 126, 037001.	2.9	14
12	Anodic oxidation of epitaxial superconductor-semiconductor hybrids. Physical Review Materials, 2021, 5, .	0.9	8
13	Hydrodynamic and Ballistic Transport over Large Length Scales in $\text{AlGaAs}$ . Physical Review Letters, 2021, 126, 076803.	2.9	42
14	Few-Electron Single and Double Quantum Dots in an $\text{InAs}$ Two-Dimensional Electron Gas. PRX Quantum, 2021, 2, .	3.5	5
15	Observation of Flat Bands in Gated Semiconductor Artificial Graphene. Physical Review Letters, 2021, 126, 106402.	2.9	7
16	Floquet-enhanced spin swaps. Nature Communications, 2021, 12, 2142.	5.8	15
17	Adiabatic quantum state transfer in a semiconductor quantum-dot spin chain. Nature Communications, 2021, 12, 2156.	5.8	34
18	Zeeman-driven parity transitions in an Andreev quantum dot. Physical Review B, 2021, 103, .	1.1	11



#	ARTICLE	IF	CITATIONS
37	Conditional teleportation of quantum-dot spin states. Nature Communications, 2020, 11, 3022.	5.8	22
38	Relating Andreev Bound States and Supercurrents in Hybrid Josephson Junctions. Physical Review Letters, 2020, 124, 226801.	2.9	53
39	Topological superconductivity in hybrid devices. Nature Physics, 2020, 16, 718-724.	6.5	105
40	Coherent Multispin Exchange Coupling in a Quantum-Dot Spin Chain. Physical Review X, 2020, 10, .	2.8	21
41	Coherent transport through a Majorana island in an Aharonov-Bohm interferometer. Nature Communications, 2020, 11, 3212.	5.8	39
42	The dependence of aluminum lattice orientation on semiconductor lattice parameter in planar InAs/Al hybrid heterostructures. Journal of Crystal Growth, 2020, 535, 125570.	0.7	1
43	Anomalous Nematic States in High Half-Filled Landau Levels. Physical Review Letters, 2020, 124, 067601.	2.9	8
44	Quantum Dots in an $\text{InSb}$ Two-Dimensional Electron Gas. Physical Review Applied, 2020, 13, .	1.5	12
45	Accurate characterization of tip-induced potential using electron interferometry. Applied Physics Letters, 2020, 117, 193101.	1.5	2
46	Ballistic superconductivity and tunable $\text{p-n}$ junctions in InSb quantum wells. Nature Communications, 2019, 10, 3764.	5.8	40
47	Topological kink plasmons on magnetic-domain boundaries. Nature Communications, 2019, 10, 4565.	5.8	14
48	The Effect of the Ion Beam Energy on M-plane InGaN Layer Preparation for STEM. Microscopy and Microanalysis, 2019, 25, 1702-1703.	0.2	0
49	Gate-defined quantum point contact in an InAs two-dimensional electron gas. Physical Review B, 2019, 100, .	1.1	11
50	Coherent spin-state transfer via Heisenberg exchange. Nature, 2019, 573, 553-557.	13.7	71
51	Electron bubbles and the structure of the orbital wave function. Physical Review B, 2019, 99, .	1.1	13
52	Evidence of topological superconductivity in planar Josephson junctions. Nature, 2019, 569, 89-92.	13.7	261
53	Aharonov-Bohm interference of fractional quantum Hall edge modes. Nature Physics, 2019, 15, 563-569.	6.5	72
54	Fast spin exchange across a multielectron mediator. Nature Communications, 2019, 10, 1196.	5.8	37

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55	Observation of new plasmons in the fractional quantum Hall effect: Interplay of topological and nematic orders. <i>Science Advances</i> , 2019, 5, eaav3407.	4.7	7
56	Integrated high electron mobility transistors in GaAs/AlGaAs heterostructures for amplification at sub-Kelvin temperatures. <i>Applied Physics Letters</i> , 2019, 114, .	1.5	4
57	Resistivity anisotropy of quantum Hall stripe phases. <i>Physical Review B</i> , 2019, 100, .	1.1	4
58	Impact of growth conditions and strain on indium incorporation in non-polar m-plane (101 $\hat{A}$ ) InGaN grown by plasma-assisted molecular beam epitaxy. <i>APL Materials</i> , 2019, 7, .	2.2	14
59	Toward durable Al-InSb hybrid heterostructures via epitaxy of 2ML interfacial InAs screening layers. <i>Physical Review Materials</i> , 2019, 3, .	0.9	7
60	Vacuum Blochâ€™Siegert shift in Landau polaritons with ultra-high cooperativity. <i>Nature Photonics</i> , 2018, 12, 324-329.	15.6	98
61	Optimization of edge state velocity in the integer quantum Hall regime. <i>Physical Review B</i> , 2018, 97, .	1.1	10
62	$\langle \text{mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"} \langle \text{mml:mi} \rangle h \langle \text{mml:mi} \rangle \langle \text{mml:mo stretchy="false"} \rangle \langle \text{mml:mi} \rangle e \langle \text{mml:mi} \rangle \langle \text{mml:math} \rangle$ Superconducting Quantum Interference through Trivial Edge States in InAs. <i>Physical Review Letters</i> , 2018, 120, 047702.	2.9	33
63	Kinetic instability of AlGaIn alloys during MBE growth under metal-rich conditions on m-plane GaN miscut towards the -c axis. <i>Journal of Applied Physics</i> , 2018, 123, 161581.	1.1	11
64	Spin of a Multielectron Quantum Dot and Its Interaction with a Neighboring Electron. <i>Physical Review X</i> , 2018, 8, .	2.8	26
65	Observation of Dirac bands in artificial graphene in small-period nanopatterned GaAs quantum wells. <i>Nature Nanotechnology</i> , 2018, 13, 29-33.	15.6	49
66	Effect of illumination on quantum lifetime in GaAs quantum wells. <i>Physical Review B</i> , 2018, 98, .	1.1	7
67	Hybridization of Subgap States in One-Dimensional Superconductor-Semiconductor Coulomb Islands. <i>Physical Review Letters</i> , 2018, 121, 256803.	2.9	34
68	A capacitance spectroscopy-based platform for realizing gate-defined electronic lattices. <i>Journal of Applied Physics</i> , 2018, 124, 124305.	1.1	0
69	Effect of density on microwave-induced resistance oscillations in back-gated GaAs quantum wells. <i>Physical Review B</i> , 2018, 98, .	1.1	1
70	Readout of singlet-triplet qubits at large magnetic field gradients. <i>Physical Review B</i> , 2018, 98, .	1.1	25
71	Intersubband Transitions in Nonpolar m-plane AlGaIn/GaN Heterostructures. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018, 215, 1700828.	0.8	7
72	Superconducting gatemon qubit based on a proximitized two-dimensional electron gas. <i>Nature Nanotechnology</i> , 2018, 13, 915-919.	15.6	138

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73	Emerging many-body effects in semiconductor artificial graphene with low disorder. Nature Communications, 2018, 9, 3299.	5.8	20
74	Direct entropy measurement in a mesoscopic quantum system. Nature Physics, 2018, 14, 1083-1086.	6.5	52
75	Electron-electron interactions and the paired-to-nematic quantum phase transition in the second Landau level. Nature Communications, 2018, 9, 2400.	5.8	22
76	High-mobility InAs 2DEGs on GaSb substrates: A platform for mesoscopic quantum transport. Physical Review Materials, 2018, 2, .	0.9	26
77	Giant Spin-Orbit Splitting in Inverted InAs/GaSb Quantum Wells. Physical Review Letters, 2017, 118, 016801.	1.1	23
78	Quantum lifetime in ultrahigh quality GaAs quantum wells: Relationship to $\hat{\Gamma}$ and impact of density fluctuations. Physical Review B, 2017, 96, .	1.1	23
79	Scaling of Majorana Zero-Bias Conductance Peaks. Physical Review Letters, 2017, 119, 136803.	2.9	338
80	Effect of density on quantum Hall stripe orientation in tilted magnetic fields. Physical Review B, 2017, 95, .	1.1	11
81	Apparent temperature-induced reorientation of quantum Hall stripes. Physical Review B, 2017, 95, .	1.1	7
82	Microwave-induced resistance oscillations in a back-gated GaAs quantum well. Physical Review B, 2017, 95, .	1.1	16
83	High-temperature resistivity measured at $\hat{\Gamma}_{1/2}$ as a predictor of the two-dimensional electron gas quality in the $N$ Landau level. Physical Review B, 2017, 95, .	1.1	6
84	High-fidelity entangling gate for double-quantum-dot spin qubits. Npj Quantum Information, 2017, 3, .	2.8	174
85	Symmetric operation of the resonant exchange qubit. Physical Review B, 2017, 96, .	1.1	34
86	Spin-orbit interaction in a dual gated InAs/GaSb quantum well. Physical Review B, 2017, 96, .	1.1	31
87	Possible nematic to smectic phase transition in a two-dimensional electron gas at half-filling. Nature Communications, 2017, 8, 1536.	5.8	22
88	Negative Spin Exchange in a Multielectron Quantum Dot. Physical Review Letters, 2017, 119, 227701.	2.9	26
89	Onset of quantum criticality in the topological-to-nematic transition in a two-dimensional electron gas at filling factor $\hat{\Gamma}_{1/2}=5/2$ . Physical Review B, 2017, 96, .	1.1	15
90	Notch filtering the nuclear environment of a spin qubit. Nature Nanotechnology, 2017, 12, 16-20.	15.6	80

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91	High-cooperativity terahertz landau polaritons in the ultrastrong coupling regime. , 2017, , .		0
92	Mobility in excess of $10^6$ cm <sup>2</sup> /V s in InAs quantum wells grown on lattice mismatched InP substrates. Applied Physics Letters, 2017, 111, .	1.5	24
93	Spectrum of the Nuclear Environment for GaAs Spin Qubits. Physical Review Letters, 2017, 118, 177702.	2.9	67
94	Dramatic enhancement of near-infrared intersubband absorption in c-plane AlInN/GaN superlattices. Applied Physics Letters, 2016, 108, .	1.5	8
95	Quasi-ballistic thermal transport in Al <sub>0.1</sub> Ga <sub>0.9</sub> N thin film semiconductors. Applied Physics Letters, 2016, 109, .	1.5	23
96	Observation of electron states of small period artificial graphene in nano-patterned GaAs quantum wells. Applied Physics Letters, 2016, 109, 113101.	1.5	10
97	Electron-Hole Asymmetric Chiral Breakdown of Reentrant Quantum Hall States. Physical Review Letters, 2016, 117, 166805.	2.9	9
98	Collective non-perturbative coupling of 2D electrons with high-quality-factor terahertz cavity photons. Nature Physics, 2016, 12, 1005-1011.	6.5	166
99	Decoupling Edge Versus Bulk Conductance in the Trivial Regime of an InAs/GaSb Quantum Well Using Corbino Ring Geometry. Physical Review Letters, 2016, 117, 077701.	2.9	38
100	Reorientation of quantum Hall stripes within a partially filled Landau level. Physical Review B, 2016, 93, .	1.1	22
101	Optical Emission Spectroscopy Study of Competing Phases of Electrons in the Second Landau Level. Physical Review Letters, 2016, 116, 016801.	2.9	11
102	Evidence for a new symmetry breaking mechanism reorienting quantum Hall nematics. Physical Review B, 2016, 93, .	1.1	18
103	Resistively detected high-order magnetoplasmons in a high-quality two-dimensional electron gas. Physical Review B, 2016, 93, .	1.1	6
104	Noise Suppression Using Symmetric Exchange Gates in Spin Qubits. Physical Review Letters, 2016, 116, 116801.	2.9	186
105	Stability of High-Density Two-Dimensional Excitons against a Mott Transition in High Magnetic Fields Probed by Coherent Terahertz Spectroscopy. Physical Review Letters, 2016, 117, 207402.	2.9	12
106	Quantized Conductance and Large $g$ -Factor Anisotropy in InSb Quantum Point Contacts. Nano Letters, 2016, 16, 7509-7513.	4.5	49
107	Modified MBE hardware and techniques and role of gallium purity for attainment of two dimensional electron gas mobility $>35 \times 10^6$ cm <sup>2</sup> /V s in AlGaAs/GaAs quantum wells grown by MBE. Journal of Crystal Growth, 2016, 441, 71-77.	0.7	50
108	Observation of a transition from a topologically ordered to a spontaneously broken symmetry phase. Nature Physics, 2016, 12, 191-195.	6.5	68

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109	Transport of a sliding Wigner crystal in the four flux composite fermion regime. <i>Physical Review B</i> , 2015, 92, .	1.1	12
110	Shubnikov-de Haas oscillations in a two-dimensional electron gas under subterahertz radiation. <i>Physical Review B</i> , 2015, 92, .	1.1	11
111	Gapped excitations of unconventional fractional quantum Hall effect states in the second Landau level. <i>Physical Review B</i> , 2015, 92, .	1.1	11
112	Coherent vertical electron transport and interface roughness effects in AlGaIn/GaN intersubband devices. <i>Journal of Applied Physics</i> , 2015, 118, .	1.1	22
113	In-surface confinement of topological insulator nanowire surface states. <i>Applied Physics Letters</i> , 2015, 107, 121605.	1.5	14
114	Gate-tunable high mobility remote-doped InSb/In $\alpha$ xAlxSb quantum well heterostructures. <i>Applied Physics Letters</i> , 2015, 106, .	1.5	29
115	Electric and Magnetic Tuning Between the Trivial and Topological Phases in InAs/GaSb Double Quantum Wells. <i>Physical Review Letters</i> , 2015, 115, 036803.	2.9	82
116	Induced superconductivity in high-mobility two-dimensional electron gas in gallium arsenide heterostructures. <i>Nature Communications</i> , 2015, 6, 7426.	5.8	97
117	Superradiant Decay of Cyclotron Resonance of Two-Dimensional Electron Gases. <i>Physical Review Letters</i> , 2014, 113, 047601.	2.9	88
118	Low-temperature illumination and annealing of ultrahigh quality quantum wells. <i>Physical Review B</i> , 2014, 90, .	1.1	16
119	$\langle \text{mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"} \rangle \langle \text{mml:mrow} \rangle \langle \text{mml:mi} \rangle \frac{1}{2} \langle \text{mml:mi} \rangle \langle \text{mml:mo} \rangle = \langle \text{mml:mn} \rangle 5 \langle \text{mml:mn} \rangle \langle \text{mml:mo} \rangle / \langle \text{mml:mo} \rangle \langle \text{mml:mn} \rangle 2$ Quantum Hall State in the Presence of Alloy Disorder. <i>Physical Review Letters</i> , 2014, 112, 116804.	2.9	30
120	Full control of quadruple quantum dot circuit charge states in the single electron regime. <i>Applied Physics Letters</i> , 2014, 104, .	1.5	39
121	Impact of short-range scattering on the metallic transport of strongly correlated two-dimensional holes in GaAs quantum wells. <i>Physical Review B</i> , 2014, 90, .	1.1	2
122	Surface topography and chemistry shape cellular behavior on wide band-gap semiconductors. <i>Acta Biomaterialia</i> , 2014, 10, 2455-2462.	4.1	24
123	Molecular Beam Epitaxy of Ultra-High-Quality AlGaAs/GaAs Heterostructures: Enabling Physics in Low-Dimensional Electronic Systems. <i>Annual Review of Condensed Matter Physics</i> , 2014, 5, 347-373.	5.2	97
124	Field-effect-induced two-dimensional electron gas utilizing modulation-doped ohmic contacts. <i>Solid State Communications</i> , 2014, 197, 20-24.	0.9	7
125	Multiphoton processes at cyclotron resonance subharmonics in a two-dimensional electron system under dc and microwave excitation. <i>Physical Review B</i> , 2014, 90, .	1.1	7
126	Homogeneous AlGaIn/GaN superlattices grown on free-standing (11 $\bar{1}$ 00) GaN substrates by plasma-assisted molecular beam epitaxy. <i>Applied Physics Letters</i> , 2013, 103, .	1.5	23



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127	Comparative study of intersubband absorption in AlGa <sub>N</sub> /Ga <sub>N</sub> and AlInN/GaN superlattices: Impact of material inhomogeneities. <i>Physical Review B</i> , 2013, 88, .	1.1	28
128	Strong heavy-to-light hole intersubband absorption in the valence band of carbon-doped GaAs/AlAs superlattices. <i>Journal of Applied Physics</i> , 2013, 113, 053103.	1.1	2
129	Effects of forming gas anneal on ultrathin InGaAs nanowire metal-oxide-semiconductor field-effect transistors. <i>Applied Physics Letters</i> , 2013, 102, 093505.	1.5	23
130	Heavy-to-light hole intersubband absorption in the valence band of GaAs/AlAs heterostructures. <i>Materials Research Society Symposia Proceedings</i> , 2013, 1509, 1.	0.1	0
131	Evidence for effective mass reduction in GaAs/AlGaAs quantum wells. <i>Physical Review B</i> , 2013, 87, .	1.1	34
132	Growth and electrical characterization of Al <sub>0.24</sub> Ga <sub>0.76</sub> As/Al <sub>x</sub> Ga <sub>1-<math>\hat{x}</math></sub> As/Al <sub>0.24</sub> Ga <sub>0.76</sub> As modulation-doped quantum wells with extremely low x. <i>Applied Physics Letters</i> , 2013, 102, 252103.	1.5	13
133	Millimeter wave transmission spectroscopy of gated two-dimensional hole systems. <i>Applied Physics Letters</i> , 2012, 100, 192104.	1.5	3
134	Improvement of near-infrared absorption linewidth in AlGa <sub>N</sub> /Ga <sub>N</sub> superlattices by optimization of delta-doping location. <i>Applied Physics Letters</i> , 2012, 101, .	1.5	29
135	Contrasting energy scales of reentrant integer quantum Hall states. <i>Physical Review B</i> , 2012, 86, .	1.1	42
136	Exploration of the limits to mobility in two-dimensional hole systems in GaAs/AlGaAs quantum wells. <i>Physical Review B</i> , 2012, 85, .	1.1	16
137	Free standing GaN nano membrane by laser lift-off method. <i>Materials Research Society Symposia Proceedings</i> , 2012, 1432, 53.	0.1	4
138	20&#x2013;80nm Channel length InGaAs gate-all-around nanowire MOSFETs with EOT&#x003D;1.2nm and lowest SS&#x003D;63mV/dec. , 2012, , .		22
139	III&#x2013;V 4D transistors. , 2012, , .		0
140	Magnetoplasmon resonance in a two-dimensional electron system driven into a zero-resistance state. <i>Physical Review B</i> , 2012, 85, .	1.1	12
141	Repeatable low-temperature negative-differential resistance from Al <sub>0.18</sub> Ga <sub>0.82</sub> N/GaN resonant tunneling diodes grown by molecular-beam epitaxy on free-standing GaN substrates. <i>Applied Physics Letters</i> , 2012, 100, .	1.5	56
142	III-V gate-all-around nanowire MOSFET process technology: From 3D to 4D. , 2012, , .		30
143	Near-Infrared Absorption in Lattice-Matched AlInN/GaN and Strained AlGa <sub>N</sub> /Ga <sub>N</sub> Heterostructures Grown by MBE on Low-Defect GaN Substrates. <i>Journal of Electronic Materials</i> , 2012, 41, 881-886.	1.0	19
144	Effect of Strain on Stripe Phases in the Quantum Hall Regime. <i>Physical Review Letters</i> , 2011, 106, 016804.	2.9	50

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145	Particle-hole asymmetry of fractional quantum Hall states in the second Landau level of a two-dimensional hole system. <i>Physical Review B</i> , 2011, 83, .	1.1	7
146	Scattering mechanisms in a high-mobility low-density carbon-doped (100) GaAs two-dimensional hole system. <i>Physical Review B</i> , 2011, 83, .	1.1	15
147	Quantitative analysis of the disorder broadening and the intrinsic gap for the $\nu = 5/2$ quantum Hall state. <i>Physical Review B</i> , 2011, 84, .	1.1	38
148	Nonconventional Odd-Denominator Fractional Quantum Hall States in the Second Landau Level. <i>Physical Review Letters</i> , 2010, 105, 246808.	2.9	112
149	Magnetotransport in Zener tunneling regime in a high-mobility two-dimensional hole gas. <i>Physical Review B</i> , 2009, 80, .	1.1	10
150	Near-infrared intersubband absorption in molecular-beam epitaxy-grown lattice-matched InAlN/GaN superlattices. <i>Applied Physics Letters</i> , 2009, 94, 161111.	1.5	31
151	Cyclotron mass of two-dimensional holes in (100) oriented GaAs/AlGaAs heterostructures. <i>Applied Physics Letters</i> , 2008, 92, 012109.	1.5	17
152	Transport and Percolation in a Low-Density High-Mobility Two-Dimensional Hole System. <i>Physical Review Letters</i> , 2007, 99, 236402.	2.9	63
153	Mesoscopic structures and two-dimensional hole systems in fully field effect controlled heterostructures. <i>Applied Physics Letters</i> , 2007, 91, .	1.5	6
154	Impact of Spin-Orbit Coupling on Quantum Hall Nematic Phases. <i>Physical Review Letters</i> , 2007, 98, 206804.	2.9	24
155	Quantum transport in high mobility AlGaIn/GaN 2DEGs and nanostructures. <i>Physica Status Solidi (B): Basic Research</i> , 2006, 243, 1706-1712.	0.7	15
156	High-reflectivity ultraviolet AlGaIn/AlGaIn distributed Bragg reflectors. <i>Applied Physics Letters</i> , 2006, 88, 171101.	1.5	35
157	High mobility two-dimensional hole system in GaAs/AlGaAs quantum wells grown on (100) GaAs substrates. <i>Applied Physics Letters</i> , 2005, 86, 162106.	1.5	45
158	Acoustic phonon scattering in a low density, high mobility AlGaIn/GaN field-effect transistor. <i>Applied Physics Letters</i> , 2005, 86, 252108.	1.5	75
159	Electron mobility exceeding $160000 \text{ cm}^2/\text{Vs}$ in AlGaIn/GaN heterostructures grown by molecular-beam epitaxy. <i>Applied Physics Letters</i> , 2004, 85, 5394-5396.	1.5	57
160	Quantum and transport lifetimes in a tunable low-density AlGaIn/GaN two-dimensional electron gas. <i>Applied Physics Letters</i> , 2004, 85, 5278-5280.	1.5	29
161	Dynamics of trapped charge in GaN/AlGaIn/GaN high electron mobility transistors grown by plasma-assisted molecular beam epitaxy. <i>Applied Physics Letters</i> , 2004, 84, 422-424.	1.5	49
162	LARGE CYCLOTRON-RESONANCE LINE SPLITTING OF TWO-DIMENSIONAL ELECTRONS IN AlGaIn/GaN AND AlGaAs/GaAs HETEROSTRUCTURES. <i>International Journal of Modern Physics B</i> , 2004, 18, 3761-3768.	1.0	2

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163	Electron scattering in AlGaIn/GaN structures. Applied Physics Letters, 2004, 84, 1507-1509.	1.5	42
164	Poole-Frenkel electron emission from the traps in AlGaIn/GaN transistors. Journal of Applied Physics, 2004, 95, 6414-6419.	1.1	169
165	Electron mobility in very low density GaN <sup>+</sup> AlGaIn <sup>+</sup> GaN heterostructures. Applied Physics Letters, 2004, 85, 1722-1724.	1.5	43
166	Mechanisms of gate lag in GaN/AlGaIn/GaN high electron mobility transistors. Superlattices and Microstructures, 2003, 34, 33-53.	1.4	114
167	High power GaN/AlGaIn/GaN HEMTs operating at 2 to 25 GHz grown by plasma-assisted MBE. Physica Status Solidi A, 2003, 200, 175-178.	1.7	5
168	Nonparabolicity of the conduction band of wurtzite GaN. Applied Physics Letters, 2003, 83, 4553-4555.	1.5	36
169	Impact of Si doping on radio frequency dispersion in unpassivated GaN/AlGaIn/GaN high-electron-mobility transistors grown by plasma-assisted molecular-beam epitaxy. Applied Physics Letters, 2003, 82, 4361-4363.	1.5	57
170	Effect of dislocations on local transconductance in AlGaIn/GaN heterostructures as imaged by scanning gate microscopy. Applied Physics Letters, 2003, 83, 4559-4561.	1.5	8
171	Dislocation and morphology control during molecular-beam epitaxy of AlGaIn/GaN heterostructures directly on sapphire substrates. Applied Physics Letters, 2002, 81, 1456-1458.	1.5	35
172	High mobility AlGaIn/GaN heterostructures grown by plasma-assisted molecular beam epitaxy on semi-insulating GaN templates prepared by hydride vapor phase epitaxy. Journal of Applied Physics, 2002, 92, 338-345.	1.1	73
173	Direct imaging of reverse-bias leakage through pure screw dislocations in GaN films grown by molecular beam epitaxy on GaN templates. Applied Physics Letters, 2002, 81, 79-81.	1.5	283
174	Surface morphology and electronic properties of dislocations in AlGaIn/GaN heterostructures. Journal of Electronic Materials, 2001, 30, 110-114.	1.0	16
175	Inhomogeneous spatial distribution of reverse bias leakage in GaN Schottky diodes. Applied Physics Letters, 2001, 78, 1685-1687.	1.5	279
176	Effect of growth stoichiometry on the electrical activity of screw dislocations in GaN films grown by molecular-beam epitaxy. Applied Physics Letters, 2001, 78, 3980-3982.	1.5	116
177	High-mobility AlGaIn/GaN heterostructures grown by molecular-beam epitaxy on GaN templates prepared by hydride vapor phase epitaxy. Applied Physics Letters, 2000, 77, 2888-2890.	1.5	99
178	Photoluminescence Study of Carrier Localization and Recombination in Nearly Strain-Balanced Nonpolar InGaIn/AlGaIn Quantum Wells. Physica Status Solidi (B): Basic Research, 0, , 2100569.	0.7	1